Transistor PNP, TO-19







Pin Configuration

- 1. Emitter
- 2. Base
- 3. Collector

Features:

- PNP Silicon Planar Switching Transistor
- · Fast switching devices exhibiting short turn-off and low saturation voltage characteristics
- Switching And Linear Application DC to VHF Amplifier Applications

Absolute Maximum Ratings:

Parameter	Symbol	Value	Unit	
Collector-Emitter Voltage	V _{CEO}	60		
Collector-Base Voltage	V _{CBO}	00	V	
Emitter-Base Voltage	V _{EBO}	5		
Collector Current Continuous	I _C	600	mA	
Power Dissipation at T _a = 25°C Derate above 25°C	D	600 3.43	mW mW/°C	
Power Dissipation at T _c = 25°C Derate above 25°C	P _D	3 17.2	W mW/°C	
Operating and Storage Junction Temperature Range	T _j , T _{stg}	-65 to +200	°C	

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Electrical Characteristics: $(T_a = +25^{\circ}C \text{ unless otherwise specified})$

Darameter	Symbol	Test Condition	Value		Unit	
Parameter	Parameter Symbol Test Condition		Min.	Max.	Unii	
Collector-Emitter Voltage	V _{CEO} *	I _C = 10mA, I _B = 0		-		
Collector-Base Voltage	V _{CBO}	$I_{\rm C} = 10 \mu A, I_{\rm E} = 0$	60	-	V	
Emitter-Base Voltage	V _{EBO}	$I_{E} = 10\mu A, I_{C} = 0$	5	-		
Collector-Cut off Current	I _{CBO}	$V_{CB} = 50V, I_{E} = 0$ $T_{A} = 150^{\circ}C \ V_{CB} = 50V, I_{E} = 0$ $V_{CE} = 30V, V_{BE} = 0.5V$	-	10 10 50	nΑ μΑ nΑ	
Base Current	I _B	V _{CE} = 30V, V _{BE} = 0.5V	-	50	nA	
Collector Emitter Saturation Voltage	V _{CE(sat)} *	I _C = 150mA, I _B = 15mA	-	0.4		
Base Emitter Saturation Voltage	V _{BE(sat)} *	I _C = 150mA, I _B = 15mA I _C = 500mA, I _B = 50mA	-	1.3 2.6	V	
DC Current Gain	h _{FE}	$I_{C} = 0.1 \text{mA}, V_{CE} = 10 \text{V}$ $I_{C} = 1 \text{mA}, V_{CE} = 10 \text{V}$ $I_{C} = 10 \text{mA}, V_{CE} = 10 \text{V}$ $I_{C} = 150 \text{mA}, V_{CE} = 10 \text{V}^{*}$ $I_{C} = 500 \text{mA}, V_{CE} = 10 \text{V}^{*}$	>75 >100 >100 100 - 300 >50	-	-	
Dynamic Characteristics	•		•			
Transition Frequency	ft**	I _C = 50mA, V _{CE} = 20V, f = 100MHz	200	-	MH	
Output Capacitance	C _{ob}	V _{CB} = 10V, I _E = 0, f = 100kHz	-	8		
Input Capacitance	C _{ib}	V _{BE} = 2V, I _C = 0, f = 100kHz	-	30	pF	
Switching Time	•		•	•		
Delay Time	t _d	I _C = 150mA, I _{B1} = 15mA	-	10		
Rise Time	t _r	V _{CC} = 30V	-	40	1	
Turn-on Time	t _{on}	-	-	- 45		
Storage time	t _s	I _C = 150mA, I _{B1} = I _{B2} = 15mA	-	80	ns	
Fall Time	t _f	V _{CC} = 6V	-	30	1	
Turn-off Time	t _{off}	-	-	100		

Pulse Test: Pulse Width = $300\mu s$, Duty Cycle = 2%.



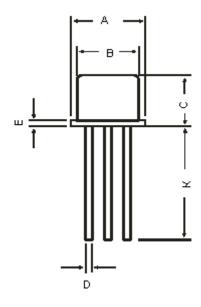


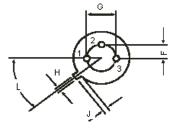
^{**} ft is defined as the frequency at which /hfe/ extrapolates to unity.

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TO-39 Metal Can Package





Dimensions	Min.	Max.
А	8.5	9.39
В	7.74	8.5
С	6.09	6.6
D	0.4	0.53
E	-	0.88
F	2.41	2.66
G	4.82	5.33
Н	0.71	0.86
J	0.73	1.02
K	12.7	-
L	42°	48°

Dimensions : Millimetres

Pin Configuration

- 1. Emitter
- 2. Base
- 3. Collector

Part Number Table

Description	Part Number
Transistor, PNP, TO-39	2N2905A

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